



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn



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Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) max}$	$I_D max$ $T_A = +25^\circ C$
-40V	80m Ω @ $V_{GS} = -10V$	-3.7 A
	150m Ω @ $V_{GS} = -4.5V$	-2.8 A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

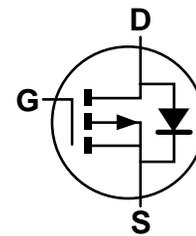
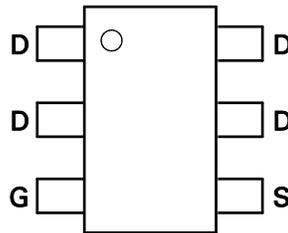
- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight 0.018 grams (Approximate)



Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

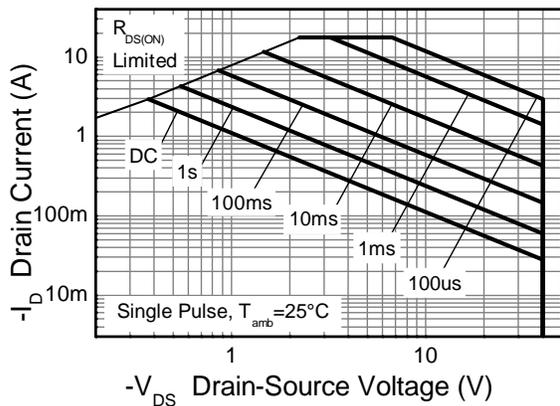
Characteristic			Symbol	Value	Unit	
Drain-Source Voltage			V_{DSS}	-40	V	
Gate-Source Voltage			V_{GS}	± 20	V	
Continuous Drain Current	$V_{GS} = 10\text{V}$	(Note 7)	I_D	-3.7	A	
		$T_A = +70^\circ\text{C}$ (Note 7)		-2.9		
		(Note 6)		-2.9		
Pulsed Drain Current	$V_{GS} = 10\text{V}$	(Note 8)	I_{DM}	-18	A	
Continuous Source Current (Body Diode)			(Note 7)	I_S	-2.6	A
Pulsed Source Current (Body Diode)			(Note 8)	I_{SM}	-18	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

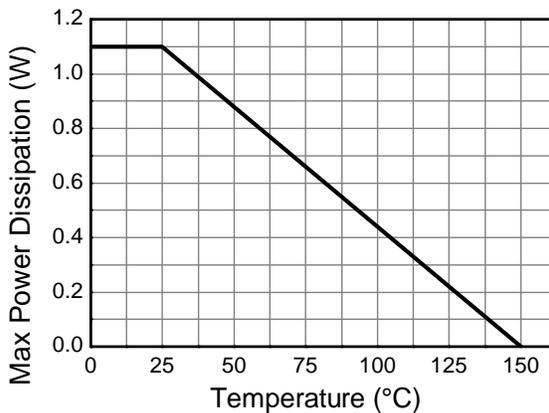
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P_D	1.1	W
			8.8	
Linear Derating Factor	(Note 7)		1.7	$\text{mW}/^\circ\text{C}$
			13.7	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	113	$^\circ\text{C}/\text{W}$
	(Note 7)		73	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 7. Same as Note 4, except the device is measured at $t \leq 5$ seconds.
 8. Same as Note 4, except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.

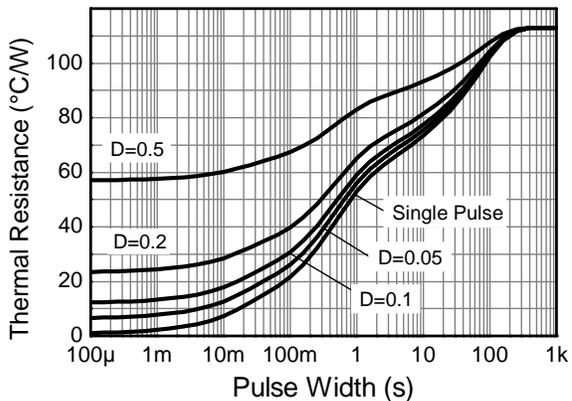
Thermal Characteristics



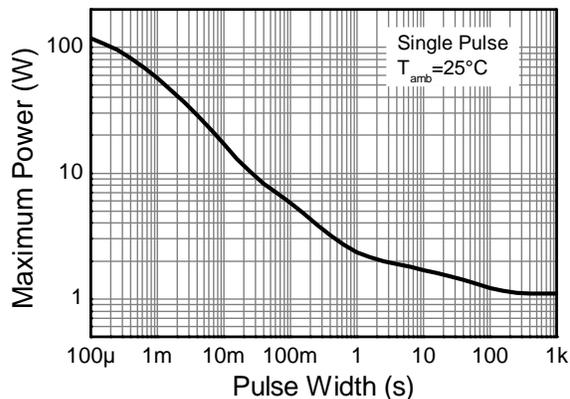
P-channel Safe Operating Area



Derating Curve



Transient Thermal Impedance



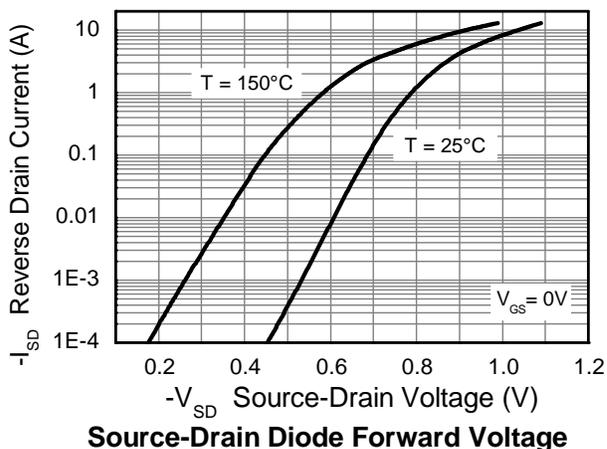
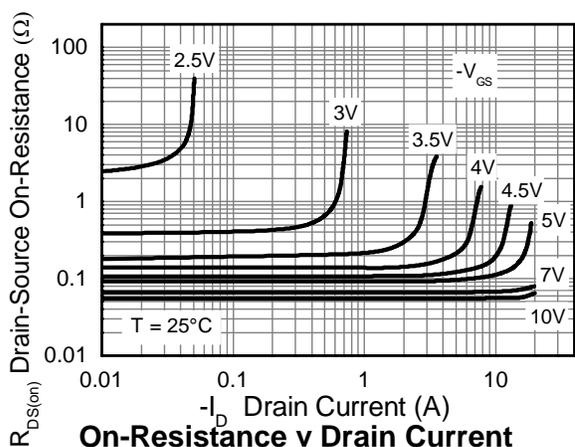
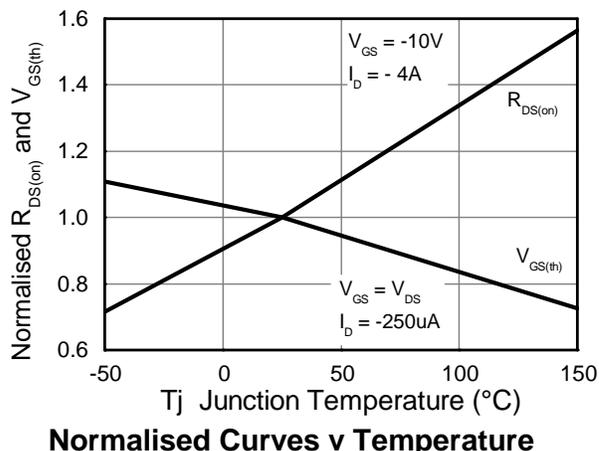
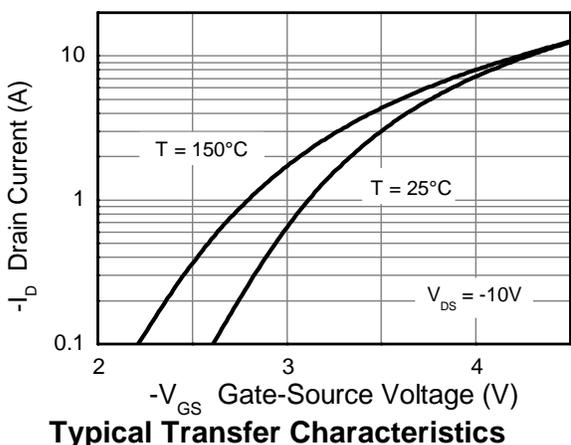
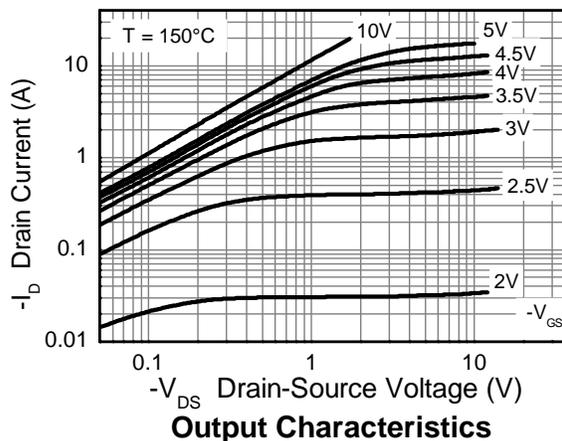
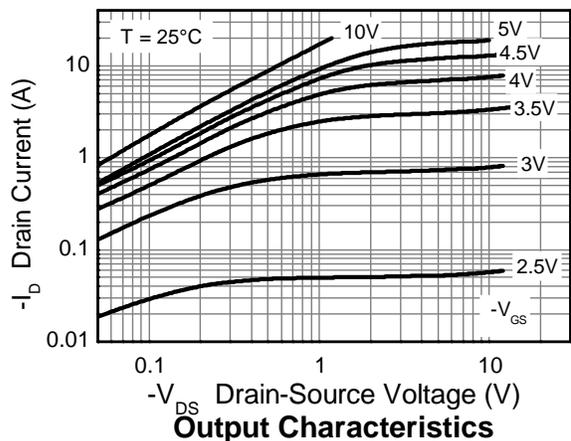
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

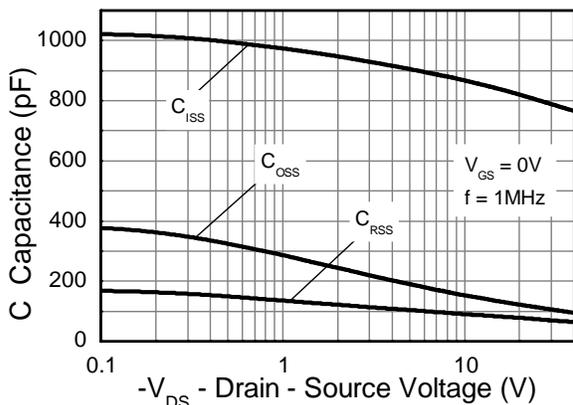
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-0.5	μA	V _{DS} = -40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	-3.0	V	I _D = -250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 9)	R _{DS(ON)}	—	—	0.080	Ω	V _{GS} = -10V, I _D = -4A
		—	—	0.150		V _{GS} = -4.5V, I _D = -2A
Forward Transconductance (Notes 9 & 10)	g _{fs}	—	7.6	—	S	V _{DS} = -15V, I _D = -4A
Diode Forward Voltage (Note 9)	V _{SD}	—	-0.86	-0.95	V	I _S = -4A, V _{GS} = 0V
Reverse Recovery Time (Note 10)	t _{rr}	—	17.4	—	ns	I _S = -1.8A, di/dt = 100A/μs
Reverse Recovery Charge (Note 10)	Q _{rr}	—	11.1	—	nC	
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	833	—	pF	V _{DS} = -20V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	122	—		
Reverse Transfer Capacitance	C _{rss}	—	78	—		
Total Gate Charge (Note 11)	Q _g	—	7	—	nC	V _{GS} = -4.5V V _{GS} = -10V V _{DS} = -20V I _D = -4A
Total Gate Charge (Note 11)	Q _g	—	15.8	—		
Gate-Source Charge (Note 11)	Q _{gs}	—	3.6	—		
Gate-Drain Charge (Note 11)	Q _{gd}	—	2.7	—		
Turn-On Delay Time (Note 11)	t _{D(on)}	—	2.5	—	ns	V _{DD} = -20V, V _{GS} = -10V I _D = -1A, R _G = 6.0Ω
Turn-On Rise Time (Note 11)	t _r	—	3.3	—		
Turn-Off Delay Time (Note 11)	t _{D(off)}	—	47	—		
Turn-Off Fall Time (Note 11)	t _f	—	21	—		

Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.
 10. For design aid only, not subject to production testing.
 11. Switching characteristics are independent of operating junction temperatures.

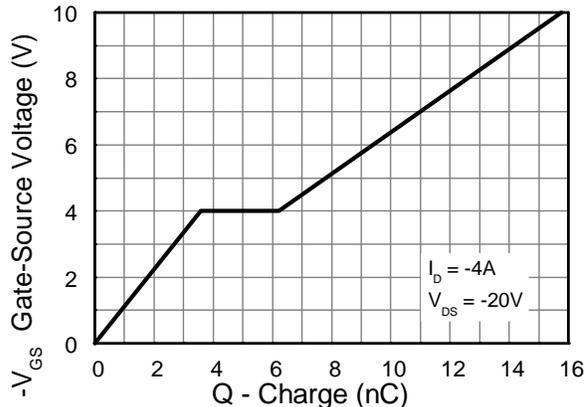
Typical Characteristics



Typical Characteristics (cont.)

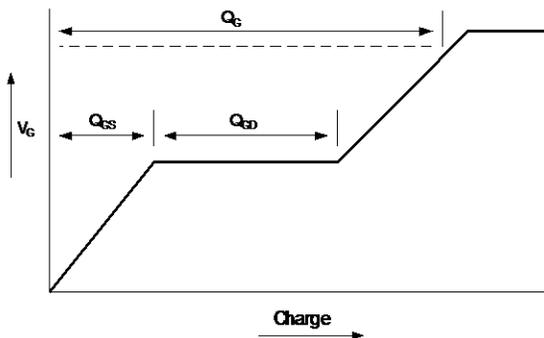


Capacitance v Drain-Source Voltage

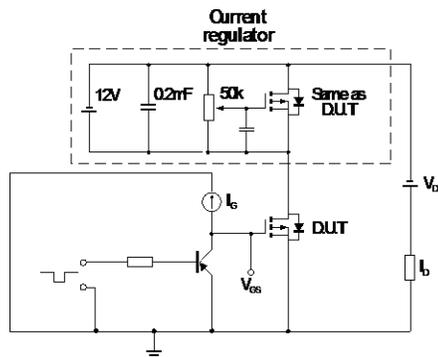


Gate-Source Voltage v Gate Charge

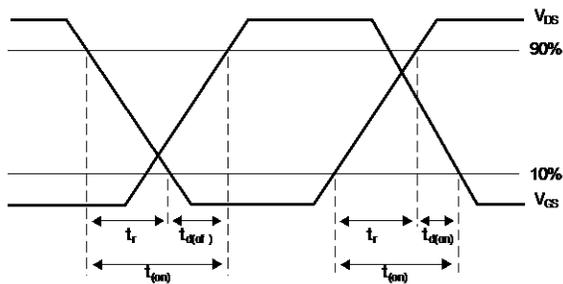
Test Circuits



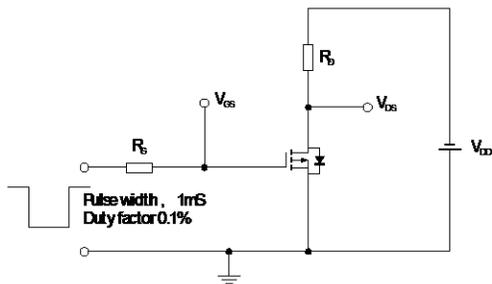
Basic gate charge waveform



Gate charge test circuit

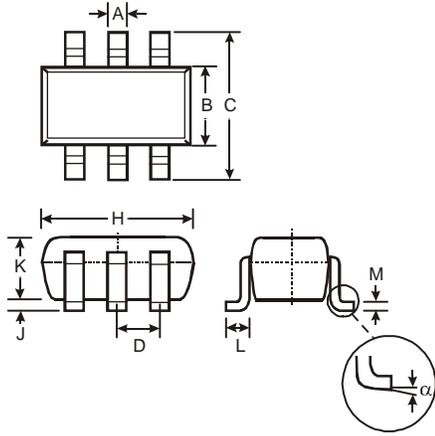


Switching time waveforms



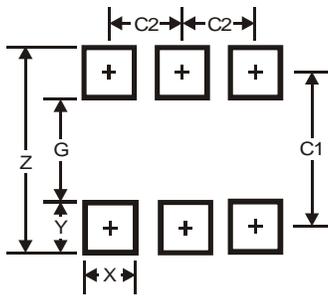
Switching time test circuit

Package Outline Dimensions



SOT26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95